

## ABSTRACT OF THE DISCLOSURE

A semiconductor laser device includes a QW active layer structure including a  $\text{Ga}_x\text{In}_{1-x}\text{As}_{1-y}\text{Sb}_y$  layer wherein  $0.3 \leq 1-x$  and  $0.003 \leq y \leq 0.008$ , or a QW active layer structure including a  $\text{Ga}_x\text{In}_{1-x}\text{As}_{1-y_1-y_2}\text{N}_{y_1}\text{Sb}_{y_2}$  layer wherein  $0.3 \leq 1-x$ ,  $0 < y_1 < 0.03$  and  $0.002 \leq y_2 \leq 0.06$ . The semiconductor laser device suppresses the three-dimensional epitaxial growth, and has superior optical characteristics including a low threshold current.

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